



deuterium, mos, annealing



















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CNF			<p><u>Multi-level metal CMOS manufacturing with deuterium for improved hot carrier reliability</u> Kizilyalli, I.C.; Weber, G.; Chen, Z.; Abeln, G.; Schonfield, M.; Kotzias, B.; Register, F.; Harris, E.; Sen, S.; Chettur, S.; Patel, M.; Stirling, L.; Huang, R.; Massengale, A.; Roy, P.K.; Higashi, G.; Foley, E.; Lee, J.; Lyding, J.; Hess, K. Electron Devices Meeting, 1998. IEDM '98 Technical Digest., International, 1998, Page(s): 935-938</p>
PER			<p><u>The time-dependence of post-irradiation interface trap build-up in deuterium-annealed oxides (n-MOSFET)</u> Saks, N.S.; Rendell, R.W. <i>applicant submitted</i> Nuclear Science, IEEE Transactions on Volume: 39 6 1-2, Dec. 1992, Page(s): 2220-2229</p>
PER			<p><u>Effects of minute impurities (H, OH, F) on SiO₂/Si interface as investigated by nuclear resonant reaction and electron spin resonance</u> Ohji, Y.; Nishioka, Y.; Yokogawa, K.; Mukai, K.; Qiu, Q.; Arai, E.; Sugano, T. Electron Devices, IEEE Transactions on Volume: 37 7, July 1990, Page(s): 1635-1642</p>
PER			<p><u>Giant isotope effect in hot electron degradation of metal oxide silicon devices</u> Hess, K.; Kizilyalli, I.C.; Lyding, J.W. Electron Devices, IEEE Transactions on Volume: 45 2, Feb. 1998, Page(s): 406-416</p>
PER			<p><u>1/f noise and radiation effects in MOS devices</u> Fleetwood, D.M.; Meisenheimer, T.L.; Scofield, J.H.</p>

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| PER |  |  | <p>Electron Devices, IEEE Transactions on
Volume: 41 11 , Nov. 1994 , Page(s): 1953 -1964</p> <p><u>Residual charges effect on the annealing behavior of Co-60 irradiated MOS capacitors</u>
Hwu, J.-G.; Lee, G.-S.; Lee, S.-C.; Wang, W.-S.
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Lelis, A.J.; Oldham, T.R.; Boesch, H.E., Jr.; McLean, F.B.
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Volume: 36 6 1-2 , Dec. 1989 , Page(s): 1808 -1815</p> |
| CNF |  |  | <p><u>Degradation of the characteristics of p/sup +/ poly MOS capacitors with NO nitrided gate oxide due to post nitrogen annealing</u>
Mazumder, M.K.; Teramoto, A.; Kobayashi, K.; Sekine, M.; Kawazu, S.; Koyama, H.
Integrated Reliability Workshop Final Report, 1997 IEEE International , 1997 , Page(s): 142 -143</p> |
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<i>Guoqiang Zhang; Rongliang Yan; Diyu Ren</i>
Microelectronics, 1995. Proceedings., 1995 20th International Conference on
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<i>Berger, M.; Shappir, L.</i>
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**High quality SiO/sub 2//Si interfaces of poly-crystalline silicon
thin film transistors by annealing in wet atmosphere**

Sano, N.; Sekiya, M.; Hara, M.; Kohno, A.; Sameshima, T.

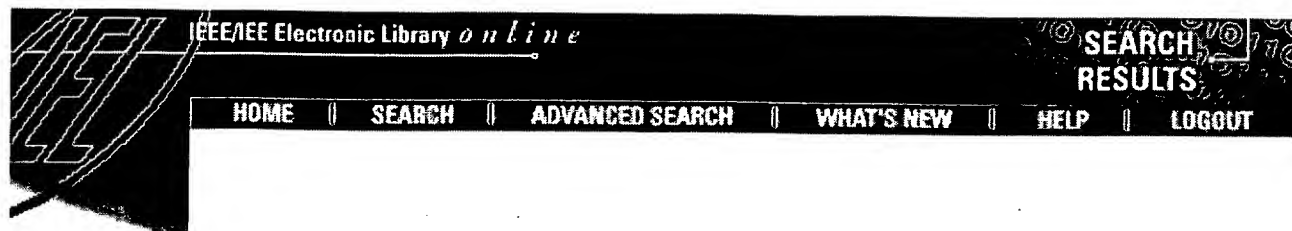
IEEE Electron Device Letters

Volume: 16 5 , May 1995 , Page(s): 157 -160

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PER			<p><u>Effects of irradiation temperature on MOS radiation response</u> Shaneyfelt, M.R.; Schwank, J.R.; Fleetwood, D.M.; Winokur, P.S. Nuclear Science, IEEE Transactions on Volume: 45 3 3 , June 1998 , Page(s): 1372 -1378</p>
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PER			<p><u>Leakage current reduction in chemical-vapor-deposited Ta/sub 2/O/sub 5/ films by rapid thermal annealing in N/sub 2/O</u> Sun, S.C.; Chen, T.F. IEEE Electron Device Letters Volume: 17 7 , July 1996 , Page(s): 355 -357</p>
PER			<p><u>Effects of post-stress hydrogen annealing on MOS oxides after /sup 60/Co irradiation or Fowler-Nordheim injection</u> Saks, N.S.; Klein, R.B.; Stahlbush, R.E.; Mrstik, B.J.; Rendell, R.W. Nuclear Science, IEEE Transactions on Volume: 40 6 1-2 , Dec. 1993 , Page(s): 1341 -1349</p>
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Lai, K.; Kumar, K.; Chou, A.; Lee, J.C.
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| PER |  |  | <p>Volume: 17 3 , March 1996 , Page(s): 82 -84</p> <p><u>Effects of nitric oxide annealing of thermally grown silicon dioxide characteristics</u></p> <p><i>Yao, Z.-Q.; Harrison, H.B.; Dimitrijevic, S.; Yeow, Y.T.</i></p> <p>IEEE Electron Device Letters</p> <p>Volume: 16 8 , Aug. 1995 , Page(s): 345 -347</p> |
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| PER |  |  | <p><u>Effects of wet oxidation/anneal on interface properties of thermally oxidized SiO₂/SiC MOS system and MOSFET's</u></p> <p><i>Yano, H.; Katafuchi, F.; Kimoto, T.; Matsunami, H.</i></p> <p>Electron Devices, IEEE Transactions on</p> <p>Volume: 46 3 , March 1999 , Page(s): 504 -510</p> |
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| PER |  |  | <p><u>Three-point method of prediction of MOS device response in space environments</u></p> <p><i>Pershenkov, V.S.; Belyakov, V.V.; Cherepko, S.V.; Shvetzov-Shilovsky, I.N.</i></p> <p>Nuclear Science, IEEE Transactions on</p> <p>Volume: 40 6 1-2 , Dec. 1993 , Page(s): 1714 -1720</p> |
| PER |  |  | <p><u>1/f noise in n- and p-channel MOS devices through irradiation and annealing</u></p> <p><i>Meisenheimer, T.L.; Fleetwood, D.M.; Shaneyfelt, M.R.; Riewe, L.C.</i></p> <p>Nuclear Science, IEEE Transactions on</p> <p>Volume: 38 6 1 , Dec. 1991 , Page(s): 1297 -1303</p> |
| PER |  |  | <p><u>Radiation hardened micron and submicron MOSFETs containing fluorinated oxides</u></p> <p><i>Nishioka, Y.; Ohyu, K.; Ohji, Y.; Kato, M.; da Silva, E.F., Jr.; Ma, T.P.</i></p> <p>Nuclear Science, IEEE Transactions on</p> <p>Volume: 36 6 1-2 , Dec. 1989 , Page(s): 2116 -2123</p> |
| PER |  |  | <p><u>Effects of N distribution on charge trapping and TDDB characteristics of N₂O annealed wet oxide</u></p> <p><i>Mazumder, M.K.; Teramoto, A.; Komori, J.; Sekine, M.; Kawazu, S.; Mashiko, Y.</i></p> <p>Electron Devices, IEEE Transactions on</p> <p>Volume: 46 6 , June 1999 , Page(s): 1121 -1126</p> |
| PER |  |  | <p><u>Low-temperature furnace-grown reoxidized nitrided oxide gate dielectrics as a barrier to boron penetration</u></p> <p><i>Fang, H.; Krisch, K.S.; Gross, B.J.; Sodini, C.G.; Chung, J.;</i></p> |

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PAT-NO: JP411087712A

DOCUMENT-IDENTIFIER: JP 11087712 A

TITLE: DEUTERIUM SUBSTANCE FOR USE IN SEMICONDUCTOR TREATMENT

PUBN-DATE: March 30, 1999

INVENTOR-INFORMATION:

NAME

CLARK, WILLIAM F
FERENCE, THOMAS G
HOOK, TERENCE B
MARTIN, DALE W**ASSIGNEE-INFORMATION:**

NAME

INTERNATL BUSINESS MACH CORP

COUNTRY

N/A

APPL-NO: JP10192725

APPL-DATE: July 8, 1998

INT-CL (IPC): H01 L 29/78; H01 L 21/324

ABSTRACT:

PROBLEM TO BE SOLVED: To ensure strong resistance against hot electron effect on the interface of silicon/silicon dioxide while suppressing damage of an element by substituting deuterium for hydrogen of a film formation reactive substance being used in production of semiconductor thereby producing a deuterium film substance at the time of film formation.

SOLUTION: A MOSFET element 100 comprises a single crystal silicon substrate 11, source-drain regions 12, 13, a gate oxide 14, a gate polysilicon 15, a gate sidewall spacer 16, a silicon nitride barrier wall 18, a passive oxide layer (e.g. SiO₂) to be bonded, and a self-aligned silicate layer 17. These components of gate oxide 14, polysilicon 15, or the like, in the element contain hydrogen molecules emitted into the oxide during annealing process. The hydrogen atom is substituted by deuterium at the time of film formation to produce a deuterium film substance. Hydrogen migrates to the interface of silicon/silicon dioxide of these component of element to produce a deuterium substance thus exhibiting resistance against heat cycle.

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Entry 11 of 66791		File: JPAB	Mar 30, 199

PUB-NO: JP411088072A
DOCUMENT-IDENTIFIER: JP 11088072 A
TITLE: MOS SEMICONDUCTOR INTEGRATED CIRCUIT

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWC	Clip Img	Image
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Entry 12 of 66791		File: JPAB	Mar 30, 199

PUB-NO: JP411088052A
DOCUMENT-IDENTIFIER: JP 11088052 A
TITLE: TEMPERATURE COMPENSATING CRYSTAL OSCILLATOR

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWC	Clip Img	Image
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Entry 13 of 66791		File: JPAB	Mar 30, 199

PUB-NO: JP411087750A
DOCUMENT-IDENTIFIER: JP 11087750 A
TITLE: MANUFACTURE OF IMPURITY SEMICONDUCTOR, P-TYPE SEMICONDUCTOR, N-TYPE SEMICONDUCTOR, AND SEMICONDUCTOR DEVICE

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Entry 14 of 66791		File: JPAB	Mar 30, 199

PUB-NO: JP411087735A
DOCUMENT-IDENTIFIER: JP 11087735 A
TITLE: SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Clip Img	Image
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☐ 15. Document ID: JP 11087730 A
Entry 15 of 66791 File: JPAB Mar 30, 199

PUB-NO: JP411087730A
DOCUMENT-IDENTIFIER: JP 11087730 A
TITLE: POLYCRYSTALLINE SEMICONDUCTOR THIN FILM, ITS FORMATION METHOD,
POLYCRYSTALLINE SEMICONDUCTOR TFT AND TFT SUBSTRATE

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Clip Img	Image
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☐ 16. Document ID: JP 11087727 A
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PUB-NO: JP411087720A
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TITLE: SEMICONDUCTOR DEVICE AND LIQUID CRYSTAL DISPLAY DEVICE

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19.

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DOCUMENT-IDENTIFIER: JP 11087711 A

TITLE: FABRICATION OF TRANSISTOR

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PUB-NO: JP411087704A

DOCUMENT-IDENTIFIER: JP 11087704 A

TITLE: SEMICONDUCTOR DEVICE AND FABRICATION THEREOF

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Entry 191 of 66791 File: JPAB Mar 16, 199

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DOCUMENT-IDENTIFIER: JP 11071137 A
TITLE: PRODUCTION OF PHOTOCATALYST THIN FILM SUPPORTING NOBLE METAL FINE PARTICLE

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWC	Image
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☐ 192. Document ID: JP 11070190 A
Entry 192 of 66791 File: JPAB Mar 16, 199

PUB-NO: JP411070190A
DOCUMENT-IDENTIFIER: JP 11070190 A
TITLE: VACUUM SUSPENSION DRIVING TYPE COATING METHOD OF GOLF CLUB HEAD

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWC	Clip Img	Image
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PUB-NO: JP411069976A
DOCUMENT-IDENTIFIER: JP 11069976 A
TITLE: COMPOSITION FOR TREATMENT OF MALIGNANT TUMOR

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWC	Image
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☐ 194. Document ID: JP 11069817 A
Entry 194 of 66791 File: JPAB Mar 9, 199

PUB-NO: JP411069817A
DOCUMENT-IDENTIFIER: JP 11069817 A
TITLE: SWITCHING ELEMENT DRIVER FOR DRIVE OF TRANSFORMER

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Clip Img	Image
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☐ 195. Document ID: JP 11069611 A
Entry 195 of 66791 File: JPAB Mar 9, 1999
PUB-NO: JP411069611A
DOCUMENT-IDENTIFIER: JP 11069611 A
TITLE: ELECTRICALLY-DRIVEN MOTOR DRIVE-TYPE STEERING APPARATUS

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Clip Img	Image
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☐ 196. Document ID: JP 11068938 A
Entry 196 of 66791 File: JPAB Mar 9, 1999
PUB-NO: JP411068938A
DOCUMENT-IDENTIFIER: JP 11068938 A
TITLE: TMN AGENT GENERATING SYSTEM

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Clip Img	Image
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☐ 197. Document ID: JP 11068695 A
Entry 197 of 66791 File: JPAB Mar 9, 1999
PUB-NO: JP411068695A
DOCUMENT-IDENTIFIER: JP 11068695 A
TITLE: IN-PHASE/ORTHOGONAL FRAME ALTERNATE ARRANGEMENT TYPE DATA COMMUNICATION SYSTEM

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Clip Img	Image
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☐ 198. Document ID: JP 11068560 A
Entry 198 of 66791 File: JPAB Mar 9, 1999
PUB-NO: JP411068560A
DOCUMENT-IDENTIFIER: JP 11068560 A
TITLE: PLL FREQUENCY SYNTHESIZER AND CHARGE PUMP CIRCUIT

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Clip Img	Image
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☐ 199. Document ID: JP 11068554 A
Entry 199 of 66791 File: JPAB Mar 9, 1999
PUB-NO: JP411068554A

DOCUMENT-IDENTIFIER: JP 11068554 A
TITLE: COUNTER AND PLL CIRCUIT

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Clip Img	Image
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200.

Document ID: JP 11068545 A

Entry 200 of 66791

File: JPAB

Mar 9, 1995

PUB-NO: JP411068545A

DOCUMENT-IDENTIFIER: JP 11068545 A

TITLE: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND CONTROL METHOD THEREFOR

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Clip Img	Image
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deuterium, MOS, annealing	66791

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JPAB,EPAB,DWPI	deuterium, mos	131285	<u>L6</u>
JPAB	deuterium, MOS, heat?	53548	<u>L5</u>
JPAB	deuterium, MOS, annealing	66791	<u>L4</u>
JPAB	deuterium, MOS	47461	<u>L3</u>
JPAB	deuterium, semiconductor, annealing or heat?	306156	<u>L2</u>
JPAB	deuterium, semiconductor	284136	<u>L1</u>

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Search Results - Record(s) 371 through 380 of 131285 returned.

371. Document ID: US 5606265 A
Entry 371 of 131285 File: EPAB Feb 25, 199

PAT-NO: US005606265A
DOCUMENT-IDENTIFIER: US 5606265 A
TITLE: Semiconductor integrated circuits with power reduction mechanism

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWC	Image
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372. Document ID: US 5606197 A
Entry 372 of 131285 File: EPAB Feb 25, 199

PAT-NO: US005606197A
DOCUMENT-IDENTIFIER: US 5606197 A
TITLE: High capacitance capacitor in an integrated function block or an integrated circuit

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWC	Image
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373. Document ID: US 5605086 A
Entry 373 of 131285 File: EPAB Feb 25, 199

PAT-NO: US005605086A
DOCUMENT-IDENTIFIER: US 5605086 A
TITLE: Compound mitre saw

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWC	Image
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374. Document ID: WO 9706564 A1
Entry 374 of 131285 File: EPAB Feb 20, 199

PAT-NO: WO009706564A1

DOCUMENT-IDENTIFIER: WO 9706564 A1
TITLE: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Image
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375. Document ID: DE 19530518 A1
Entry 375 of 131285 File: EPAB Feb 20, 199

PAT-NO: DE019530518A1
DOCUMENT-IDENTIFIER: DE 19530518 A1
TITLE: Metal carbonitride hard coating

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Image
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376. Document ID: DE 19530517 A1
Entry 376 of 131285 File: EPAB Feb 20, 199

PAT-NO: DE019530517A1
DOCUMENT-IDENTIFIER: DE 19530517 A1
TITLE: Metal carbonitride hard coating

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Image
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377. Document ID: DE 19530454 A1
Entry 377 of 131285 File: EPAB Feb 20, 199

PAT-NO: DE019530454A1
DOCUMENT-IDENTIFIER: DE 19530454 A1
TITLE: Economical continuous oxidative dehydrogenation of propane to propene in high yield

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Image
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378. Document ID: EP 758684 A1
Entry 378 of 131285 File: EPAB Feb 19, 199

PAT-NO: EP000758684A1
DOCUMENT-IDENTIFIER: EP 758684 A1
TITLE: Nickel-based superalloys with good stability at high temperatures

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Image
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379. Document ID: US 5604417 A
Entry 379 of 131285 File: EPAB Feb 18, 199

PAT-NO: US005604417A
DOCUMENT-IDENTIFIER: US 5604417 A
TITLE: Semiconductor integrated circuit device

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Image
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380.

Document ID: US 5604140 A

Entry 380 of 131285

File: EPAB

Feb 18, 199

PAT-NO: US005604140A
DOCUMENT-IDENTIFIER: US 5604140 A
TITLE: Method for forming fine titanium nitride film and method for fabricating semiconductor element using the same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Image
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Terms	Documents
deuterium, mos	131285

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=> s deuterium (1p)(annealing or heat?) and semiconductor

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894 DEUTERIUM (1P) (ANNEALING OR HEAT?)
166753 SEMICONDUCTOR
L3 83 DEUTERIUM (1P) (ANNEALING OR HEAT?) AND SEMICONDUCTOR

=> d 1-83

1. 5,910,842, Jun. 8, 1999, Focused beam spectroscopic ellipsometry method and system; Timothy R. Piwonka-Corle, et al., 356/369 [IMAGE AVAILABLE]
2. 5,909,627, Jun. 1, 1999, Process for production of thin layers of **semiconductor** material; Richard Egloff, 438/406, 522, 526, 530 [IMAGE AVAILABLE]
3. 5,909,048, Jun. 1, 1999, Micro-machining minute hollow using native oxide membrane; Rinji Sugino, 257/522, 394, 414, 417, 467, 622; 313/325 [IMAGE AVAILABLE]
4. 5,885,896, Mar. 23, 1999, Using implants to lower anneal temperatures; Randhir P. S. Thakur, et al., 438/649, 630, 659 [IMAGE AVAILABLE]
5. 5,877,070, Mar. 2, 1999, Method for the transfer of thin layers of monocrystalline material to a desirable substrate; Ulrich M. Goesele, et al., 438/458; 117/915; 438/406 [IMAGE AVAILABLE]
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7. 5,840,110, Nov. 24, 1998, Integrated circuits having mixed layered superlattice materials and precursor solutions for use in a process of making the same; Masamichi Azuma, et al., 106/287.18, 287.19 [IMAGE AVAILABLE]
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13. 5,763,514, Jun. 9, 1998, Process for producing optical resin materials with distributed refractive index; Yasuhiro Koike, 525/265, 277, 306, 932 [IMAGE AVAILABLE]
14. 5,760,366, Jun. 2, 1998, Thin film forming apparatus using laser and magnetic field; Kenyu Haruta, et al., 219/121.68 [IMAGE AVAILABLE]
15. 5,745,536, Apr. 28, 1998, Secondary electron ion source neutron generator; John P. Brainard, et al., 376/114, 108 [IMAGE AVAILABLE]
16. 5,729,580, Mar. 17, 1998, Hydrogen ion array acceleration generator and method; Gregory L. Millspaugh, 376/114, 115, 146 [IMAGE AVAILABLE]
17. 5,713,979, Feb. 3, 1998, Heat treatment facility for synthetic vitreous silica bodies; Robert Nicholson, et al., 65/424, 374.13, 374.15, 426, 427, 519, 530, 540 [IMAGE AVAILABLE]
18. 5,711,998, Jan. 27, 1998, Method of polycrystalline silicon hydrogenation; Paul Kevin Shufflebotham, 427/535, 527; 438/162, 475, 798 [IMAGE AVAILABLE]
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22. 5,662,814, Sep. 2, 1997, Micro-machining minute hollow using native oxide membrane; Rinji Sugino, 216/2, 39, 56, 60; 438/701, 708, 719 [IMAGE AVAILABLE]
23. 5,622,567, Apr. 22, 1997, Thin film forming apparatus using laser; Kazuyoshi Kojima, et al., 118/726; 427/596; 505/732 [IMAGE AVAILABLE]
24. 5,608,526, Mar. 4, 1997, Focused beam spectroscopic ellipsometry method and system; Timothy R. Piwonka-Corle, et al., 356/369, 73 [IMAGE AVAILABLE]
25. 5,581,350, Dec. 3, 1996, Method and system for calibrating an ellipsometer; Xing Chen, et al., 356/369 [IMAGE AVAILABLE]
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27. 5,530,319, Jun. 25, 1996, Power supply circuit for a discharge lamp and use of and method of operating the same; Volker Adam, et al., 315/106, 94, 107, 224, 306, 308, DIG.7 [IMAGE AVAILABLE]
28. 5,510,277, Apr. 23, 1996, Surface treatment for silicon substrates; John E. Cunningham, et al., 438/707; 134/1.3; 438/974 [IMAGE AVAILABLE]
29. 5,506,857, Apr. 9, 1996, **Semiconductor** Laser Pumped molecular gas lasers; Richard A. Meinzer, 372/55, 101 [IMAGE AVAILABLE]
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44. 5,087,815, Feb. 11, 1992, High resolution mass spectrometry of recoiled ions for isotopic and trace elemental analysis; J. Albert Schultz, et al., 250/309, 287, 307 [IMAGE AVAILABLE]
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52. 4,910,436, Mar. 20, 1990, Wide area VUV lamp with grids and purging jets; George J. Collins, et al., 315/111.81; 118/50.1; 204/164; 313/231.61, 362.1; 315/111.21 [IMAGE AVAILABLE]
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56. 4,742,276, May 3, 1988, Regulated deuterium arc supply system; Yeegee Ku, 315/106, 94, 175, 205, 224, 308 [IMAGE AVAILABLE]
57. 4,661,836, Apr. 28, 1987, Fabricating integrated circuits; Joseph Mun, 257/712, 664, 684, 713, 728 [IMAGE AVAILABLE]
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62. 4,503,328, Mar. 5, 1985, Evaluation of the interaction with radiant energy of substances traversed by a borehole; Jacob Neufeld, 250/262, 269.7 [IMAGE AVAILABLE]
63. 4,417,180, Nov. 22, 1983, Lamp firing apparatus; Morteza M. Chamran, et al., 315/175, 171, 173, 205, 360 [IMAGE AVAILABLE]
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